HW # 06 Abdullah MEMISOGLU 171024001 U1: Design a common-source NMOS amplifier as Shaun in fig P7.67 to give a passband gain of 2016 20 4 Aprol = 30, Zincmil > 100 ks. a low 3-dB frequency of FL 410kHz, and a high 3-dB frequency of FH = 20deHz. IDSS = 12.5 mA, ID = IMA Vp=-].5V &RL Vo 6>> ROHRL, RL>> RD R6-Ivery large KD = 1042, gm = 4.9 × 10-3 Gozin Tain WL, WH VE gain bulunecale Re- 500 le le 1062 No-562 Analiz sonucilari bilinmesi gereken deure: th=90kHz, fcz = 0.99KHz Transresister

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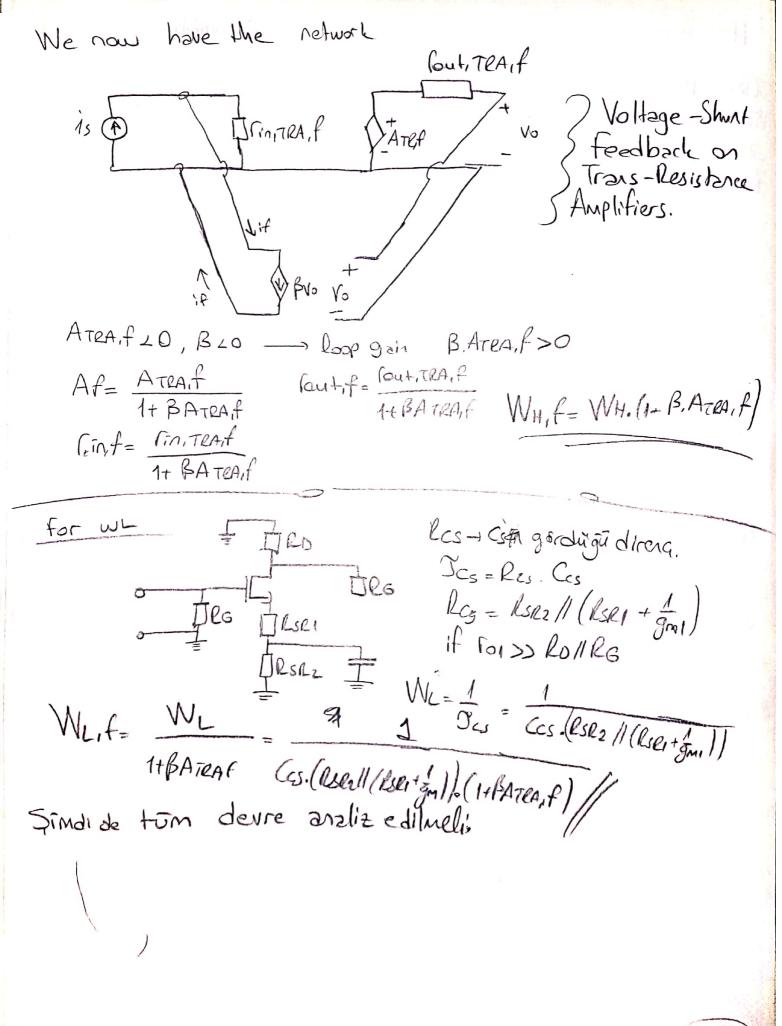
ATEA, F CI = 8nF

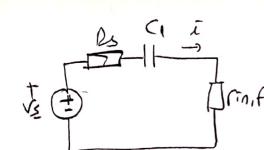
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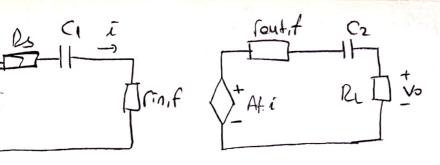
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Rodel

Rodel PINITRA, F = RG routiteA,f = LG//ROUTITEA = REMPONICON(1+9milse1)  $\frac{Y_{d1}}{Y_{gn}} = \frac{-9MJ}{1+gmllse_1} \left[ \frac{|Qn||R6||[nort(1+gmllse_1)]}{1+gmllse_1} \right]$ ATRA, F = -9m RG [RG/1RD/[Coi(1+9n] RsR1 >> gmi Miller Cgd1,g1 = 6gd1(1- Vd1) lcgd,g,=lc, Tcgd,g,=lcgd,g,.Cgd,d1 J= RG. Cgd1. (1- Vd1) WH= 1 = RG. Cgd1. (1- Vd1) B=1 - for feedback network







$$\frac{V_0}{V_S} = ? \qquad \vec{t} = \frac{V_S}{R_{J} + F_{i} n_i f}$$

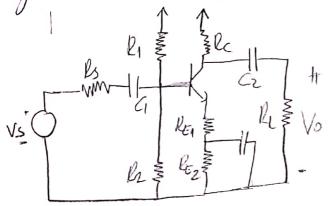
Q2. A two stage amplifier is shown in fig. p. 7.71. The parameters are Ls = 162, Ru = 500h, Rz1 = 500h, RD1=10h, R12=500h, Rz2 = 500h BD2=1562, R=1062, gm1=20mA/V, gm2=50mA/V, C1=1MF, C2=1MF C3 = 30 MF, C9d1 = 6922 = 2pf C9s1 = C9sz = 5pf. Calculate the low 3dB Frequency fi and high cutoff frequency fr. VOD 15V 7 VAS SCTC RCI, CI'in gordique direnci. (Sci=Rci. Ci) RC1 = RS + R11/1R21, RC2, Cznun gardugui direnc. (Tcz=Rcz.C2) u (TC3 = RC3. C3) RC2 = RD1 1101 + P21/1R22 RC3, C3hin " hc3 = (RL+ Rollion)  $A_{m} = \frac{\sqrt{91}}{\sqrt{5}} \cdot \frac{\sqrt{61}}{\sqrt{91}} \cdot \frac{\sqrt{62}}{9\sqrt{92}}$  (0.110.1)Widbard gain (R11/1/21 + Rs), (-gm1 (RD1/1/321/1/22)). (-gm2 (RDD/1/RLL/1/02)) Cgar, gr = Miller capacitance at ga, cgdz, gz = Miller capacitance at gz Cgd1, g1 = Cgd1 (1 - Vd1 ) = Cgd1 (1+ 9m1 (Roll 1221 // R221/ Rol)

(gdz,gz = Cgdz(1 - Vdz) = Cgdz(1+9mz(RD//Rc//102)

Rc9d1, g1 = Rs // Ru//Rzi 12 c garige = R21 || R22 || R01 || roa Jcgd1,91 = Rcgd1,91. Cgd1,91 Jegarign = ( ls || R11 || R21). Cgd1 g1 5 cgd1, g1 = (1 W2 /1 500 W2 /1 500 W2 / 500 W /1 500 W 2162 3cgd1191 = 1000-2×10-12.200 Jcg 21,91 = 2×10-7 Cgdzigz = Cgdz. (1 - Vdz ) Jegdzidz = Regdzigz. Cgdzigz Jcgdzdz = (l21//l22//lD2//101). Gdz. (1+9m2.(lop//l/g//101) (02) Jcgdz,dz= (500/1/5006/1/601):2×10-12 (1+50mA/V (156/1/602)) × 250km. 210-12. 300 Jegdzidz = 150 × 10-6 = 1.5 × 10-4 WH = 1 = 6666.66 Scgd1,91 + Ocgdudz ~ Scgd2, dz

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O3: For Probs 8.54 - 8.59 involving BJT amplifiers, use transistors whose Parameters are Bf=100, Cje=8pf at VBE=0.5V, CM=4pf at VCB=5V, Ccs=4pf at Vcs=8V, Bf=100, Vje=Vjc=Vjs=0.8V, and hoe=1/ro=5m V at VcE=10V The transition frequency is f7=300MH= at VcE=20V, IC=10mA. The substate is connected to the ground. Assume IC=5mA, Vcc=15V, VBE=0.4V, Rs=102 and Ri=10th. Use SPICED to check your design by plotting the frequency response and give an approximate cost estimate.



Rin, b1 = FITI [1+9MIREN] AD

SCTC WL = Trut Top len =) Chin goldings direng. (Sch = Ren. Ch)

RC1 = Rs + Roll Rell Ringht = [Rs+ Roll Rell (1874 [1+9miles]) = Ren

lin, a = FOI (Hgmiles)

Rez - Crima gordipur diem. Rez = Ret Rell Rinica

OCTC account for only Gu (Miller effect For 61)

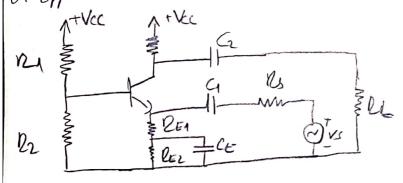
Cu.b1 = Cu [1+ gmales (lc///[[ron (1+gmales)]])

RCM, SA = RA 11 R2 11 R2 11 R2 11 R2 11 R2 11 R2 11 (FIT [A+9 MIREA]). SM [1+ SMI)
-(RC | | Re | | [100 + (149 m)])

6

J= RI 112/12/1 (1# [1+9MIREN]). GM [1+ 9ml ( PC 11/2 /1/201 (1+9m RE))])

Qy For Probs. 8,54-8,59 involving BIT amplifiers, use transistors whose parameters De Bf= 100, Cje = 8PF at VBE = 0.5V, Cu = 4PF at VCB = 5V, Cs = 4PF at VCS = 8V Bf = 100, Vje = Vjc = Vjs = 0.8V, and hoe = 1/10 = 5MZ-cd VCE = 10V. The Hansity's frequency is fr = 300 MHz of VCE = 20V, Ic=10mA, The substrate is connected to the grand. Assure Ic= SMA, Vec=15V, VBE=0.7V, Rs=161, Re=104, Use SPICE to check your design by plotting the frequency response and give en approximate cost éstimate.



SCTC RCE, CEhin gordiges direna. DCE = REE.CE

RCE = REZU[REI+ Ps//gmi]

RC1, Cin gardigis direna. JC1 = RC1. Ci

la= ls + lea /1 gmi

Rez, G nun gordigs drens.

RC2 - Re+ Re 11 [101 (1+ gmila)]

LCB, CB'n In Gördsigs direis.

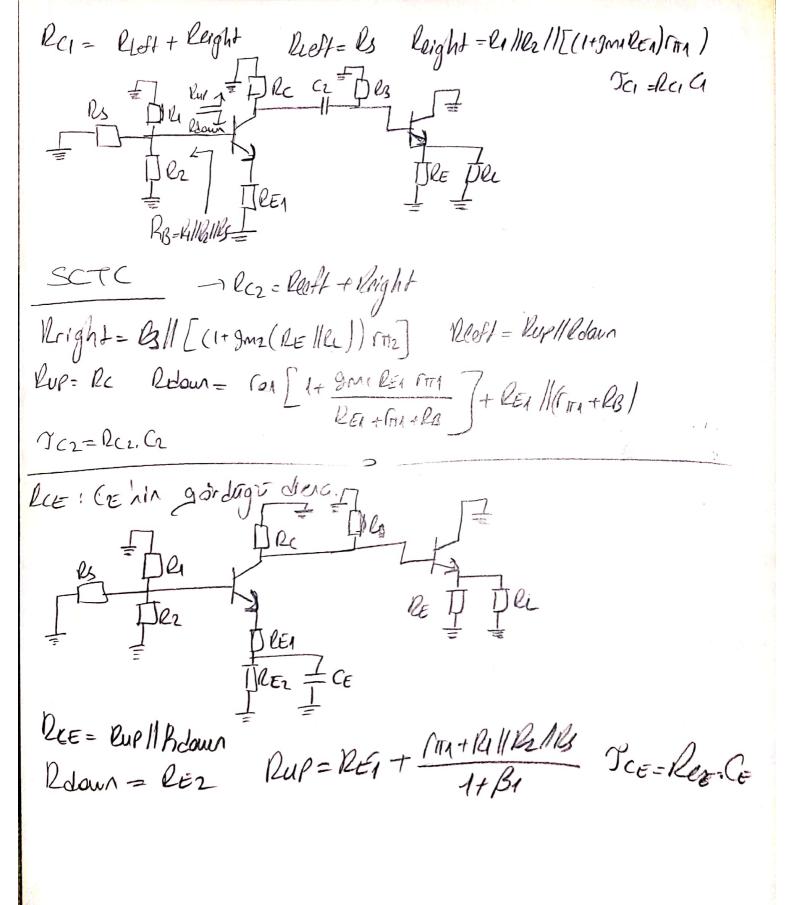
RCB = RI 1/2/1/ [1+Gmiles) /

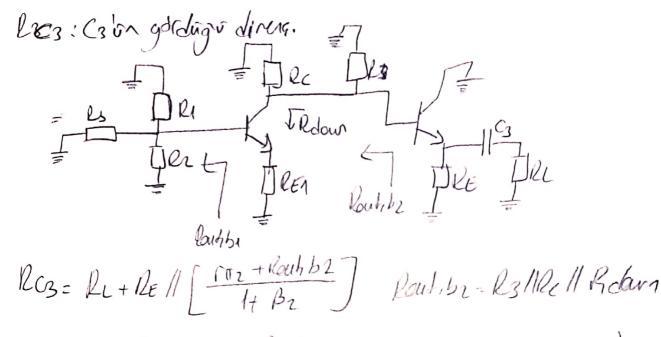
$$W_{L} = \frac{1}{\Im c_{\varepsilon}} + \frac{1}{\Im c_{1}} + \frac{1}{\Im c_{2}} + \frac{1}{\Im c_{8}}$$



MINDER BRADIM Am = Vo = leall gmi
Reall gmi + ls -gm1(Rc/14) So ve Su yok god ad SCTC Le OCTC lyu: Gu'non gord. direra. PCM = Rell Rell [Noi (Itgmi Real] ) WH = 1

SGM+ JGM RCH = REA 1/RS 11 gmn For Probs. 8,54-8,59 involving BIT amplifiers, use transistor whose parameterare Bf = 100, Cje = 8pF 2t VBE=0.5V, Cu = 4pF 2t VcB = 5V, Ccs = 4pF 2t Vcs=8V, Bf=100 Vje=Vjs=0.8V 2nd hoe=1/ro=5MZr of VcE=lov. The transition frequency is fragments 21 VCE = 20V, Ic=10m A. The substrate is connected to the ground. Assume Ic=5mA VCC=15V, VBE=0.7V, ls=162, ond le=1042. Use SPICE to check your design. plee of Vec





WIH approximation

$$\frac{CCTC}{WH = \frac{1}{5gu_1b_1} = \frac{1}{lgu_1,b_1} = ls ||Q_1|| ||Q_1||| ||Q_1|| ||Q_1||$$